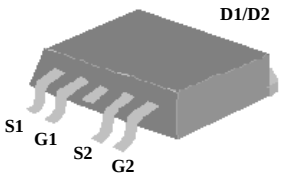
Complementary N and P-channel Enhancement-mode Power MOSFETs

Simple Drive Requirement

Good Thermal Performance

Fast Switching Performance

RoHS-compliant, halogen-free



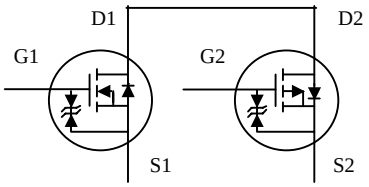
TO-252-4L

N-CH	BV_{DSS}	40V
	$R_{DS(ON)}$	26mΩ
	I_D	8.3A
P-CH	BV_{DSS}	-40V
	$R_{DS(ON)}$	40mΩ
	I_D	-7A

Description

Advanced Power MOSFETs from APEC provide the designer with the best combination of fast switching, low on-resistance and cost-effectiveness.

The AP4525GEH-A-HF-3 is in a four-lead TO-252 package, which is widely used for commercial and industrial surface-mount applications, and is well suited for applications such as DC and servo motor drives.



Absolute Maximum Ratings

Symbol	Parameter	Rating		Units
		N-channel	P-channel	
V_{DS}	Drain-Source Voltage	40	-40	V
V_{GS}	Gate-Source Voltage	±16	±16	V
I_D at T_A=25°C	Continuous Drain Current[3]	8.3	-7.0	A
I_D at T_A=70°C	Continuous Drain Current[3]	6.6	-5.6	A
I_{DM}	Pulsed Drain Current[1]	50	-50	A
P_D at T_A=25°C	Total Power Dissipation	3.125		W
	Linear Derating Factor	0.025		W/°C
T_{STG}	Storage Temperature Range	-55 to 150		°C
T_J	Operating Junction Temperature Range	-55 to 150		°C

Thermal Data

Symbol	Parameter	Value	Unit
Rthj-c	Maximum Thermal Resistance, Junction-case	8	°C/W
Rthj-a	Maximum Thermal Resistance, Junction-ambient[3]	40	°C/W

Ordering Information

AP4525GEH-A-HF-3TR RoHS-compliant TO-252-4L, shipped on tape and reel (3000 pcs/reel)

No longer recommended for new designs - use AP4543GEH-HF-3TR

N-channel Electrical Specifications at T_j=25°C (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250uA	40	-	-	V
$\Delta BV_{DSS}/\Delta T_j$	Breakdown Voltage Temperature Coefficient	Reference to 25°C, I_D=1mA	-	0.03	-	V/°C
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=10V, I_D=6A	-	-	26	mΩ
		V_{GS}=4.5V, I_D=4A	-	-	32	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250uA	1	-	3	V
g_{fs}	Forward Transconductance	V_{DS}=10V, I_D=6A	-	6	-	S
I_{DSS}	Drain-Source Leakage Current	V_{DS}=40V, V_{GS}=0V	-	-	1	uA
	Drain-Source Leakage Current (T_j=70°C)	V_{DS}=32V, V_{GS}=0V	-	-	25	uA
I_{GSS}	Gate-Source Leakage	V_{GS}=±16V	-	-	±30	uA
Q_g	Total Gate Charge[2]	I_D=6A	-	9	14	nC
Q_{gs}	Gate-Source Charge	V_{DS}=20V	-	1.5	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	V_{GS}=4.5V	-	4	-	nC
$t_{d(on)}$	Turn-on Delay Time[2]	V_{DS}=20V	-	7	-	ns
t_r	Rise Time	I_D=6A	-	20	-	ns
$t_{d(off)}$	Turn-off Delay Time	R_G=3Ω , V_{GS}=10V	-	20	-	ns
t_f	Fall Time	R_D=3.3Ω	-	4	-	ns
C_{iss}	Input Capacitance	V_{GS}=0V	-	580	930	pF
C_{oss}	Output Capacitance	V_{DS}=25V	-	100	-	pF
C_{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	70	-	pF
R_g	Gate Resistance	f=1.0MHz	-	2	3	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage[2]	I_S=15A, V_{GS}=0V	-	-	1.3	V
t_{rr}	Reverse Recovery Time[2]	I_S=6A, V_{GS}=0V	-	20	-	ns
Q_{rr}	Reverse Recovery Charge	dI/dt=100A/µs	-	15	-	nC

Notes:

1. Pulse width limited by maximum junction temperature.
2. Pulse width≤300us, duty cycle≤ 2%.
3. Values are the same for both N-CH and P-CH MOSFETs, when mounted on 2oz FR4 board, t ≤10s.

P-channel Electrical Specifications at T_j=25°C (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=-250uA	-40	-	-	V
$\Delta BV_{DSS}/\Delta Tj$	Breakdown Voltage Temperature Coefficient	Reference to 25°C, I_D=-1mA	-	-0.03	-	V/°C
$R_{DS(ON)}$	Static Drain-Source On-Resistance[2]	V_{GS}=-10V, I_D=-5A	-	-	40	mΩ
		V_{GS}=-4.5V, I_D=-3A	-	-	60	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=-250uA	-0.8	-	-2.5	V
g_{fs}	Forward Transconductance	V_{DS}=-10V, I_D=-5A	-	5	-	S
I_{DSS}	Drain-Source Leakage Current	V_{DS}=-40V, V_{GS}=0V	-	-	-1	uA
	Drain-Source Leakage Current (T_j=70°C)	V_{DS}=-32V, V_{GS}=0V	-	-	-25	uA
I_{GSS}	Gate-Source Leakage	V_{GS}=±16V	-	-	±30	uA
Q_g	Total Gate Charge[2]	I_D=-5A	-	9	24	nC
Q_{gs}	Gate-Source Charge	V_{DS}=-20V	-	2	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	V_{GS}=-4.5V	-	5	-	nC
$t_{d(on)}$	Turn-on Delay Time[2]	V_{DS}=-20V	-	8.5	-	ns
t_r	Rise Time	I_D=-5A	-	15	-	ns
$t_{d(off)}$	Turn-off Delay Time	R_G=3Ω , V_{GS}=-10V	-	27	-	ns
t_f	Fall Time	R_D=4Ω	-	25	-	ns
C_{iss}	Input Capacitance	V_{GS}=0V	-	760	1220	pF
C_{oss}	Output Capacitance	V_{DS}=-20V	-	150	-	pF
C_{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	105	-	pF
R_g	Gate Resistance	f=1.0MHz	-	6	9	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage[2]	I_S=-12A, V_{GS}=0V	-	-	-1.3	V
t_{rr}	Reverse Recovery Time[2]	I_S=-5A, V_{GS}=0V	-	20	-	ns
Q_{rr}	Reverse Recovery Charge	dI/dt=-100A/μs	-	16	-	nC

Notes:

1.Pulse width limited by maximum junction temperature.

2.Pulse width≤300us, duty cycle≤ 2%.

3.Values are the same for both N-CH and P-CH MOSFETs, when mounted on 2oz FR4 board, t ≤10s.

Typical N-channel Electrical Characteristics

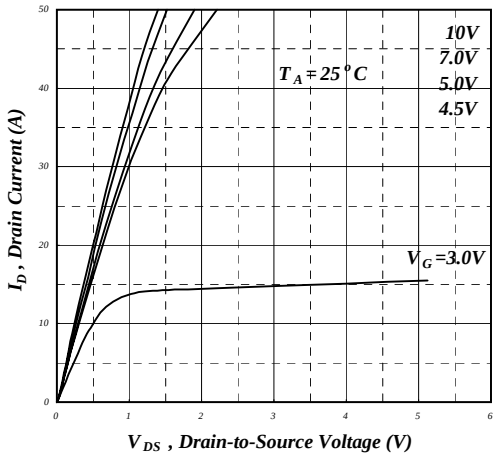


Fig 1. Typical Output Characteristics

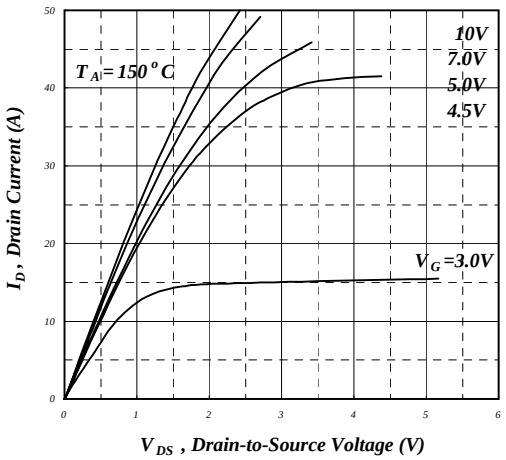


Fig 2. Typical Output Characteristics

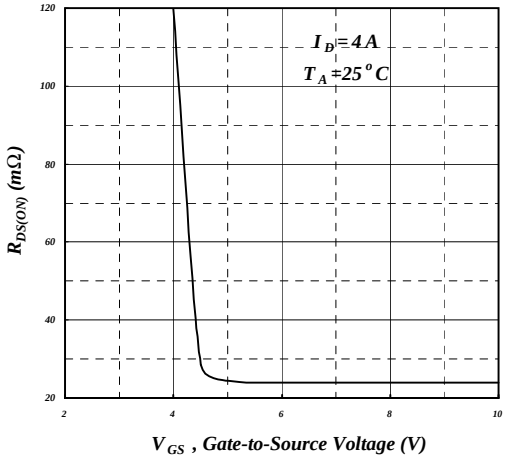


Fig 3. On-Resistance vs. Gate Voltage

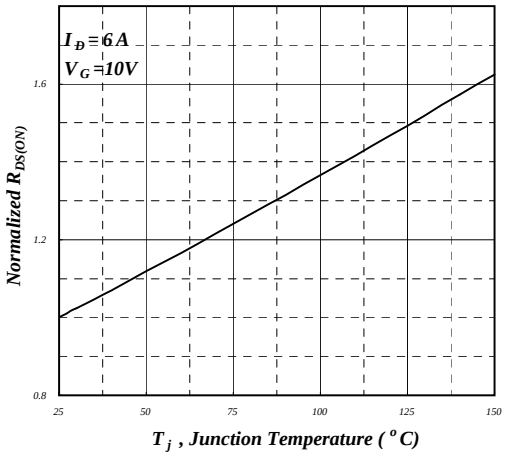


Fig 4. Normalized On-Resistance vs. Junction Temperature

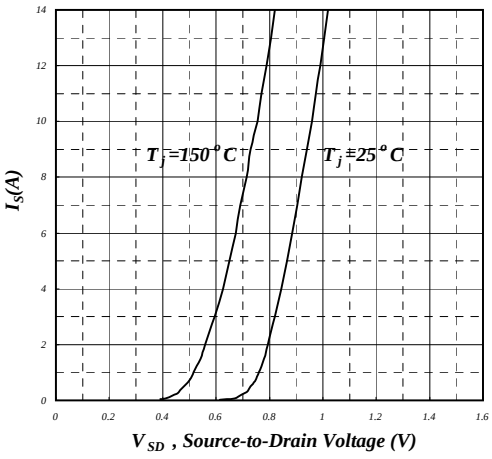


Fig 5. Forward Characteristic of Reverse Diode

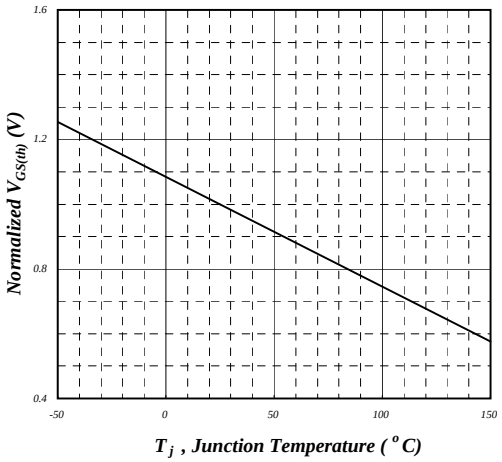


Fig 6. Gate Threshold Voltage vs. Junction Temperature

Typical N-channel Electrical Characteristics (cont.)

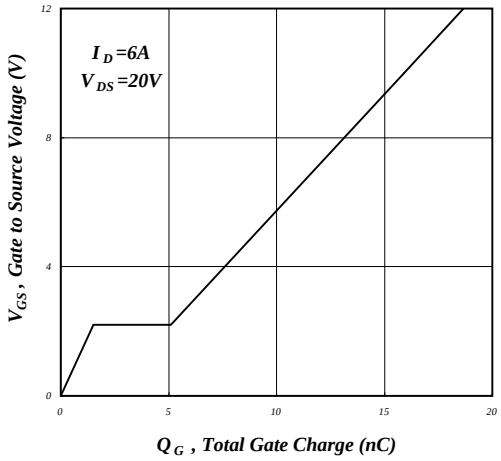


Fig 7. Gate Charge Characteristics

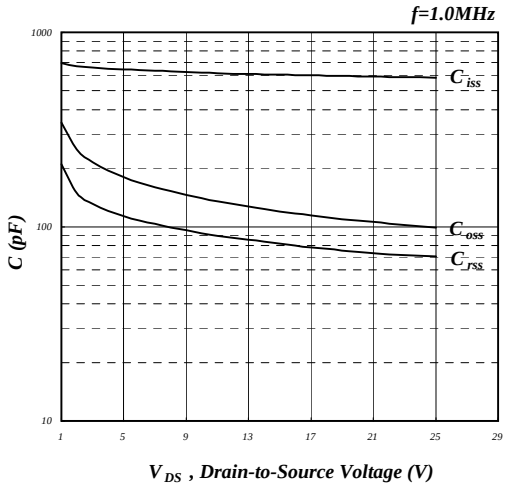


Fig 8. Typical Capacitance Characteristics

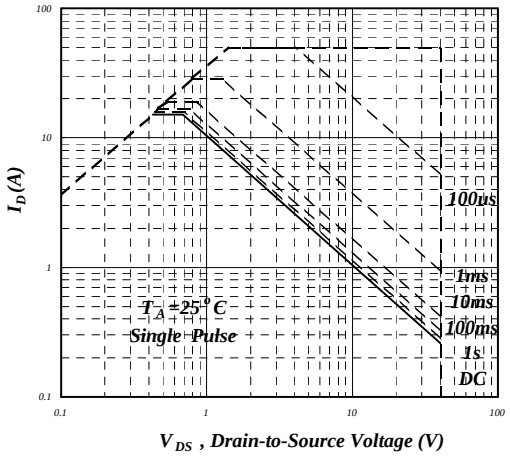


Fig 9. Maximum Safe Operating Area

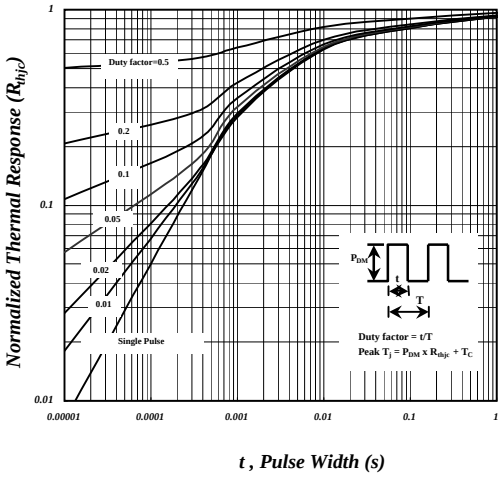


Fig 10. Effective Transient Thermal Impedance

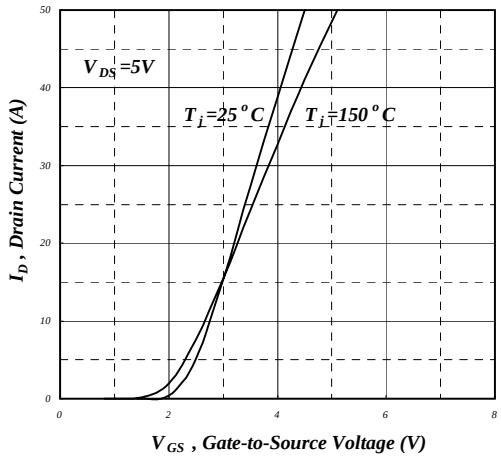


Fig 11. Transfer Characteristics

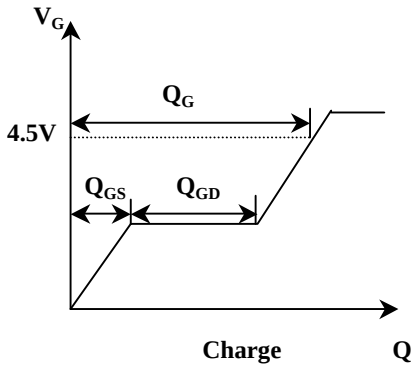


Fig 12. Gate Charge Waveform

Typical P-channel Electrical Characteristics

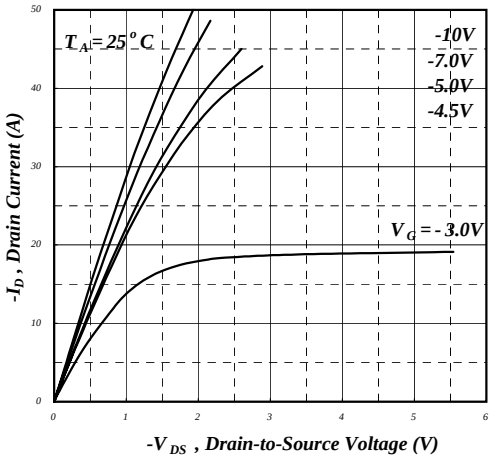


Fig 1. Typical Output Characteristics

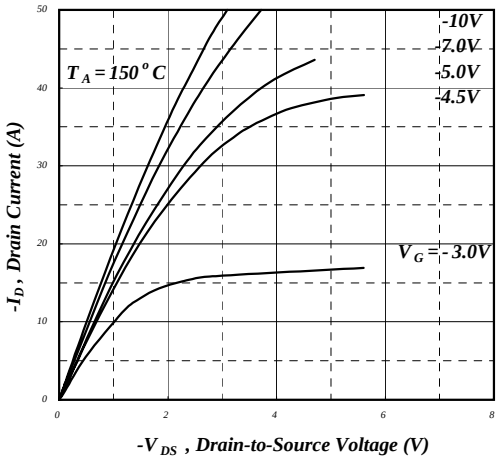


Fig 2. Typical Output Characteristics

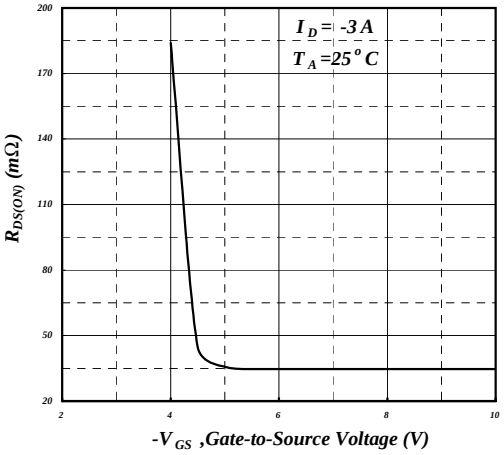


Fig 3. On-Resistance vs. Gate Voltage

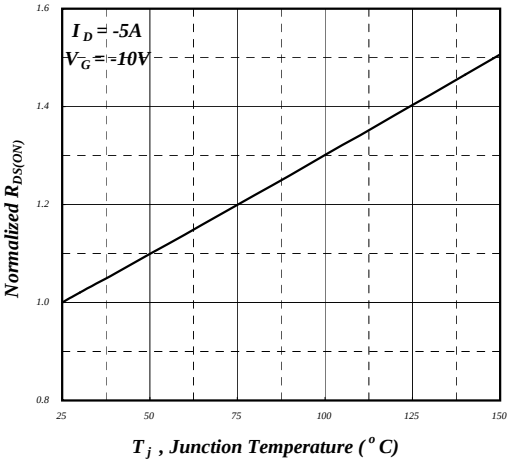


Fig 4. Normalized On-Resistance vs. Junction Temperature

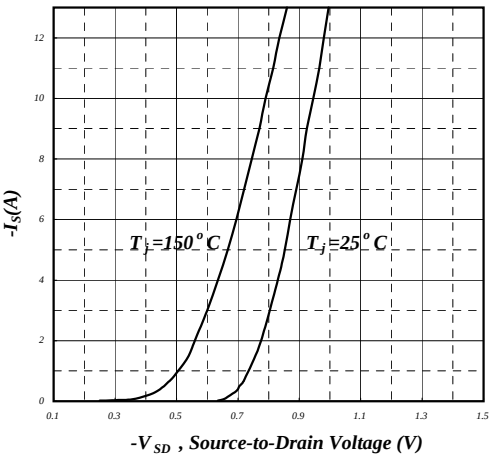


Fig 5. Forward Characteristic of Reverse Diode

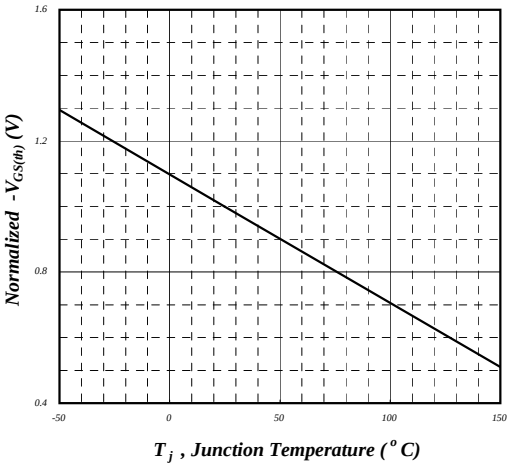


Fig 6. Gate Threshold Voltage vs. Junction Temperature

Typical P-channel Electrical Characteristics (cont.)

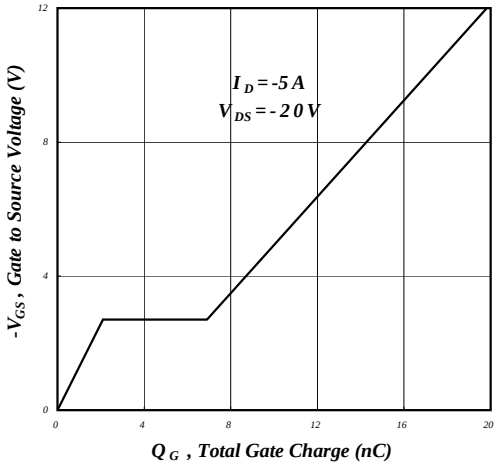


Fig 7. Gate Charge Characteristics

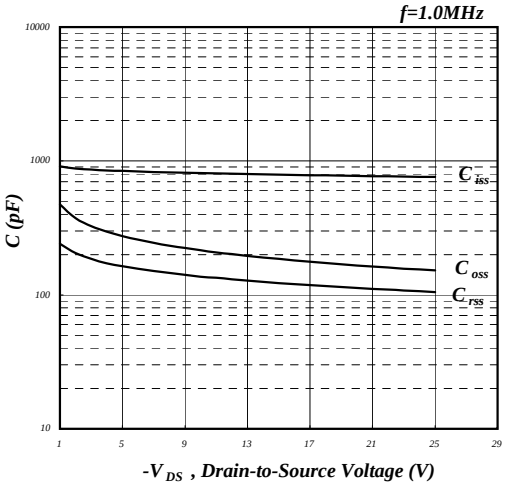


Fig 8. Typical Capacitance Characteristics

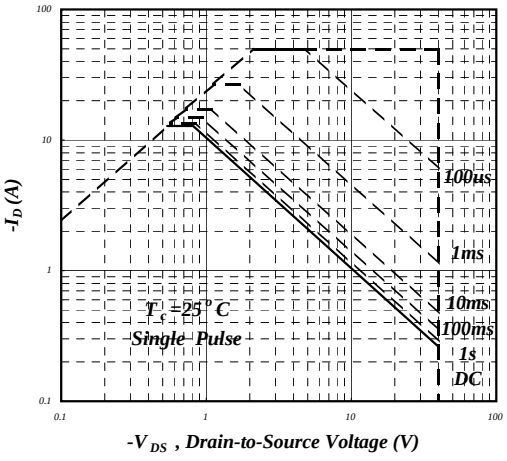


Fig 9. Maximum Safe Operating Area

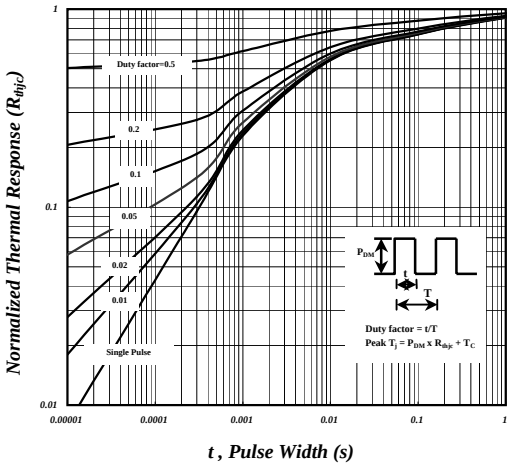


Fig 10. Effective Transient Thermal Impedance

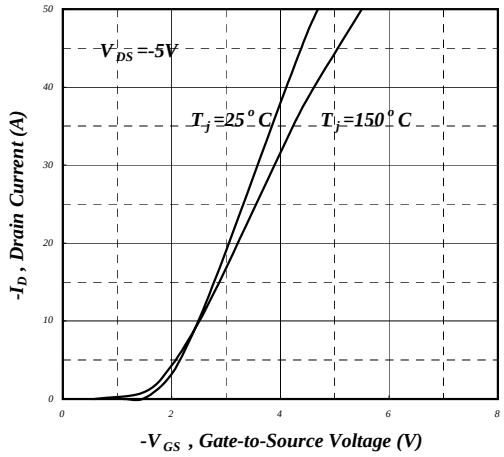


Fig 11. Transfer Characteristics

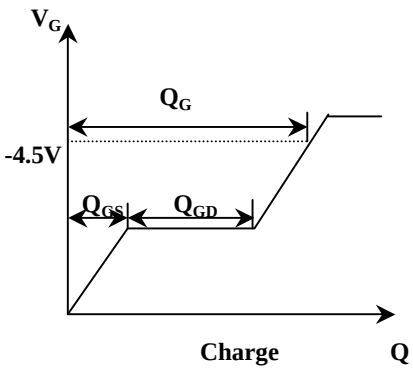
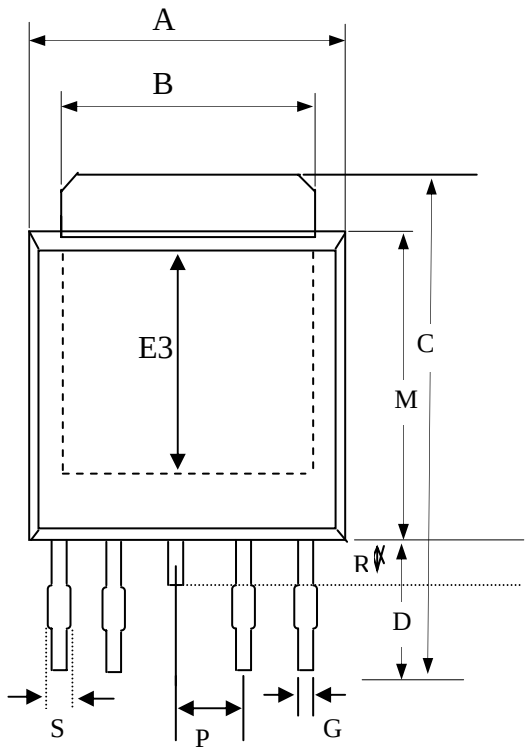
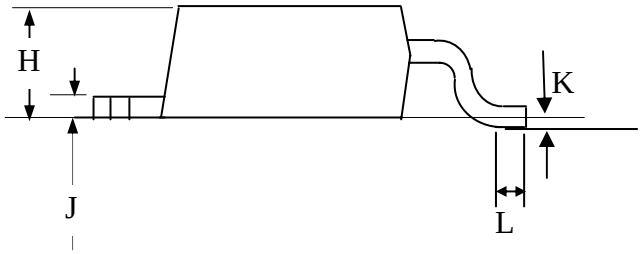


Fig 12. Gate Charge Waveform

Package Dimensions: TO-252-4L

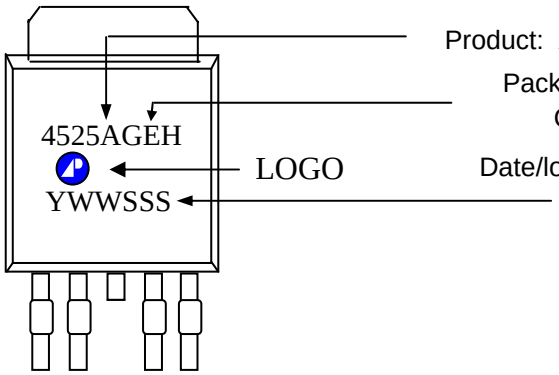




SYMBOLS	Millimeters		
	MIN	NOM	MAX
A	6.40	6.6	6.80
B	5.2	5.35	5.50
C	9.40	9.80	10.20
D	2.40	2.70	3.00
P		1.27 REF.	
S	0.50	0.65	0.80
E3	3.50	4.00	4.50
R	0.80	1.00	1.20
G	0.40	0.50	0.60
H	2.20	2.30	2.40
J	0.45	0.50	0.55
K	0.00	0.075	0.15
L	0.90	1.20	1.50
M	5.40	5.60	5.80

1. All dimensions are in millimeters.
2. Dimensions do not include mold protrusions.

Marking Information:



Product: AP4525-A

Package:
GEH = RoHS-compliant halogen-free TO-252-4L

Date/lot code (YWWSSS)
Y: Last digit of the year
WW: Work week
SSS: Lot code sequence